

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J328R

#### 1. Applications

· Power Management Switches

#### 2. Features

- (1) 1.5-V drive
- (2) Low drain-source on-resistance

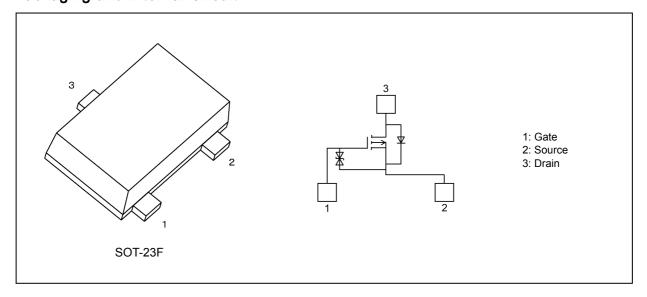
:  $R_{DS(ON)}$  = 88.4 m $\Omega$  (max) (@ $V_{GS}$  = -1.5 V)

 $R_{DS(ON)} = 56.0 \text{ m}\Omega \text{ (max) } (@V_{GS} = -1.8 \text{ V})$ 

 $R_{DS(ON)} = 39.7 \text{ m}\Omega \text{ (max) } (@V_{GS} = -2.5 \text{ V})$ 

 $R_{DS(ON)} = 29.8 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.5 \text{ V})$ 

#### 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	-20	V
Gate-source voltage				$V_{GSS}$	±8	V
Drain current (DC)			(Note 1)	I <sub>D</sub>	-6.0	Α
Drain current (pulsed)			(Note 1), (Note 2)	$I_{DP}$	-24.0	
Power dissipation			(Note 3)	$P_{D}$	1	W
Power dissipation	t =	= 10 s	(Note 3)		2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: Pulse width (PW)  $\leq$  10  $\mu$ s, duty  $\leq$  1%

Note 3: Device mounted on a FR4 board.

(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad : 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance	(Note 1)	R <sub>th(ch-a)</sub>	125	°C/W

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-1	μА
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 5 V	-15	_	_	V
Gate threshold voltage	(Note 2)	V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$	-0.3	_	-1.0	V
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D = -3.0 \text{ A}, V_{GS} = -4.5 \text{ V}$	_	24.9	29.8	mΩ
			I <sub>D</sub> = -2.5 A, V <sub>GS</sub> = -2.5 V	_	31.1	39.7	
			I <sub>D</sub> = -1.5 A, V <sub>GS</sub> = -1.8 V	_	38.8	56.0	
			I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.5 V	_	47.4	88.4	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -1.0 \text{ A}$	4.5	9.1	_	S

Note 1: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

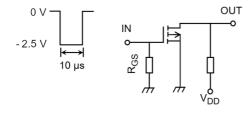
Note 2: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 , V <sub>GS</sub> = 0 V,	_	840	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		99		
Output capacitance	C <sub>oss</sub>		_	118		
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -10 V, $I_{D}$ = -2.0 A, $V_{GS}$ = 0 to -2.5 V, $R_{GS}$ = 4.7 $\Omega$		32		ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, V <sub>IN</sub> : $t_r$ , $t_f$ < 5 ns Common source	_	107	_	

#### 6.3. Switching Time Test Circuit



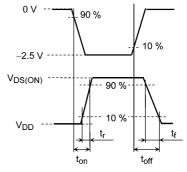


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

#### 6.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = -10 \text{ V}, I_{DS} = -4.0 \text{ A},$	_	12.8	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = -4.5 V	_	1.4	_	
Gate-drain charge	Q <sub>gd</sub>		_	3.0	_	



## 6.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_{DR} = 6.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	0.87	1.2	V

Note 1: Pulse measurement.

## 7. Marking

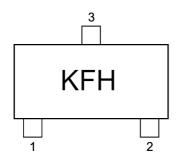


Fig. 7.1 Marking



#### 8. Characteristics Curves (Note)

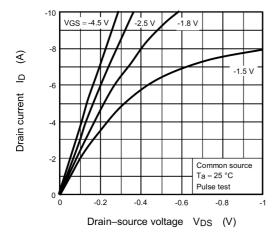


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

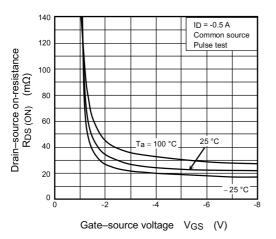


Fig. 8.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

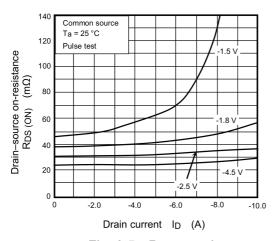


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

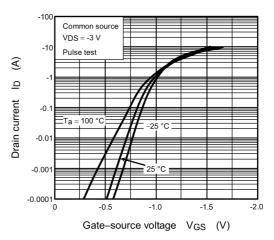


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

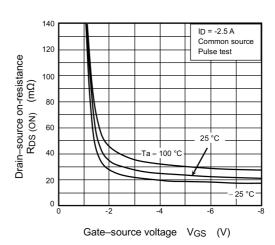


Fig. 8.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

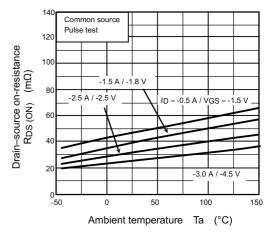


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



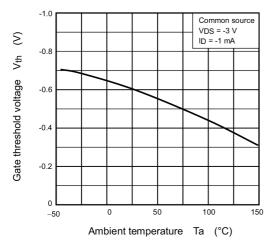


Fig. 8.7 V<sub>th</sub> - T<sub>a</sub>

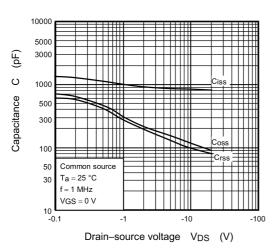


Fig. 8.9 C - V<sub>DS</sub>

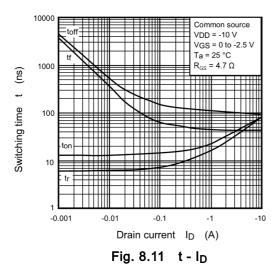


Fig. 8.8 |Y<sub>fs</sub>| - I<sub>D</sub>

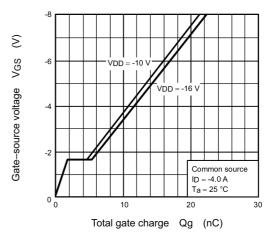


Fig. 8.10 Dynamic Input Characteristics

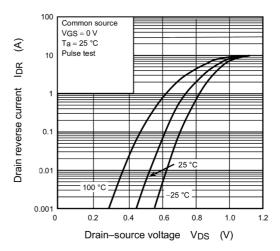


Fig. 8.12 IDR - VDS



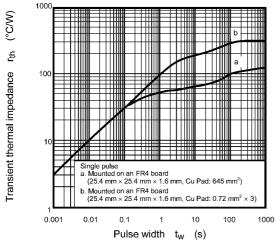


Fig. 8.13 rth - tw

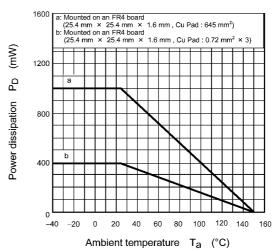


Fig. 8.14 P<sub>D</sub> - T<sub>a</sub>

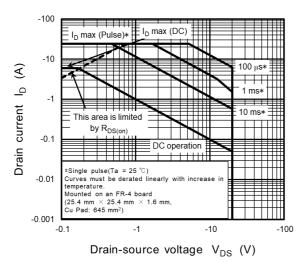


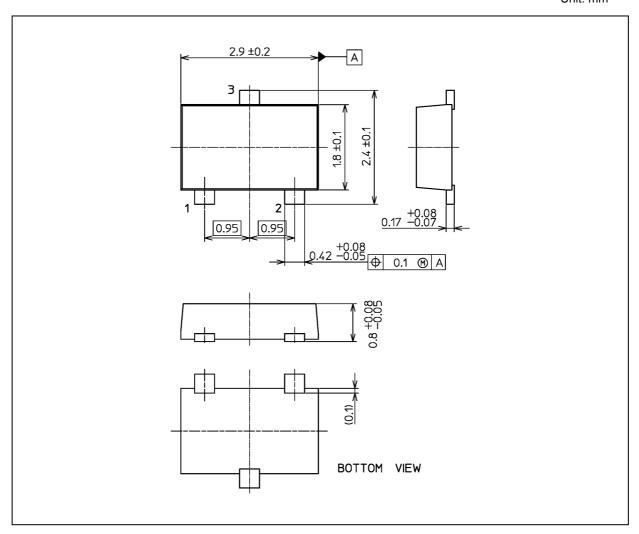
Fig. 8.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	



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